

# **Isc N-Channel MOSFET Transistor**

### IPA65R099C6

#### FEATURES

- With TO-220F package
- · Low input capacitance and gate charge
- Reduced switching and conduction losses
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



· Switching applications

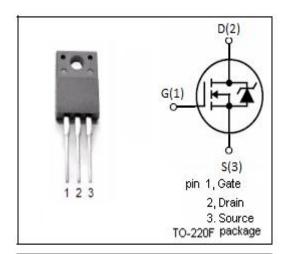


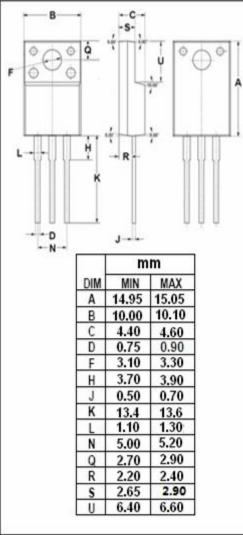
ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

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|--|--|---------|------|--|--|--|
| SYMBOL   | PARAMETER  | VALUE   | UNIT |  |  |  |
| V <sub>DSS</sub>                                     | Drain-Source Voltage   | 650     | V    |  |  |  |
| V <sub>GSS</sub>                                     | Gate-Source Voltage  | ±30 V   |      |  |  |  |
| I <sub>D</sub>                                       | Orain Current-Continuous @Tc=25℃ 38<br>(V <sub>GS</sub> at 10V) Tc=100℃ 24 |         | А    |  |  |  |
| I <sub>DM</sub>                                      | Drain Current-Single Pulsed  | 115     | А    |  |  |  |
| P <sub>D</sub>                                       | Total Dissipation @T <sub>C</sub> =25℃                                     | 35      | W    |  |  |  |
| Тј   | Max. Operating Junction Temperature  | 150     | °C   |  |  |  |
| T <sub>stg</sub>                                     | Storage Temperature  | -55~150 | °C   |  |  |  |

#### • THERMAL CHARACTERISTICS

| SYMBOL    | PARAMETER                             | MAX | UNIT |
|-----------|---------------------------------------|-----|------|
| Rth(ch-c) | Channel-to-case thermal resistance    | 3.6 | °C/W |
| Rth(ch-a) | Channel-to-ambient thermal resistance | 80  | °C/W |







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### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

| SYMBOL              | PARAMETER                      | CONDITIONS   | MIN | ТҮР | MAX      | UNIT |
|---------------------|--------------------------------|--|-----|-----|----------|------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> =1mA   | 650 |     |          | V    |
| V <sub>GS(th)</sub> | Gate Threshold Voltage         | V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =1.2mA  | 2.5 |     | 3.5      | V    |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance     | V <sub>GS</sub> = 10V; I <sub>D</sub> =12.8A   |     | 89  | 99       | mΩ   |
| I <sub>GSS</sub>    | Gate-Source Leakage Current    | V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0V  |     |     | ±0.1     | μА   |
| I <sub>DSS</sub>    | Drain-Source Leakage Current   | V <sub>DS</sub> = 650V; V <sub>GS</sub> = 0V;Tj=25℃<br>V <sub>DS</sub> = 650V; V <sub>GS</sub> = 0V; Tj=150℃ |     |     | 1<br>100 | μА   |
| V <sub>SDF</sub>    | Diode forward voltage          | I <sub>SD</sub> =19.2A, V <sub>GS</sub> = 0 V  |     | 0.9 |          | V    |

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